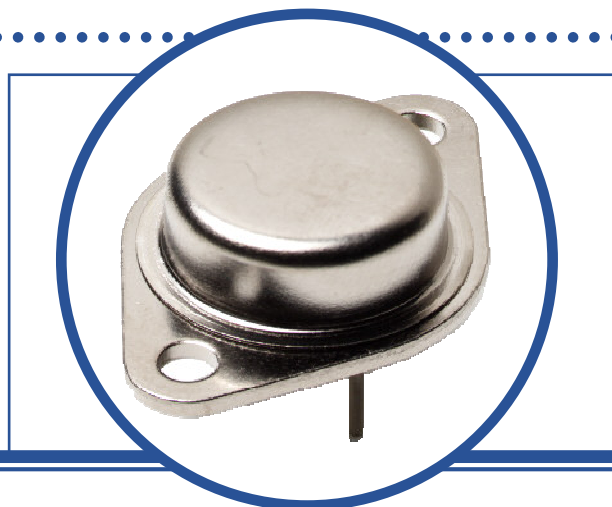


SILICON POWER NPN TRANSISTOR

2N6673

- High Voltage
- Hermetic Low Profile TO3 Metal Package.
- Designed For Power Switching and Linear Applications
- Screening Options Available



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage	650V
V_{CEX}	Collector – Emitter Voltage	650V
V_{CEO}	Collector – Emitter Voltage	400V
V_{EBO}	Emitter – Base Voltage	8V
I_C	Continuous Collector Current	8A
I_B	Base Current	4A
P_D	Total Power Dissipation at $T_A = 25^\circ\text{C}$	6W
	Derate Above 25°C	0.0343 W/ $^\circ\text{C}$
P_D	Total Power Dissipation at $T_C = 25^\circ\text{C}$	150W
	Derate Above 25°C	0.857 W/ $^\circ\text{C}$
T_J	Junction Temperature Range	-65 to +150 $^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65 to +150 $^\circ\text{C}$

THERMAL PROPERTIES

Symbols	Parameters	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction To Case	1.17	$^\circ\text{C/W}$

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



SILICON POWER NPN TRANSISTOR 2N6673

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

Symbols	Parameters	Test Conditions	Min.	Typ	Max.	Units
$V_{(BR)CEO}^{(1)}$	Collector-Emitter Breakdown Voltage	$I_C = 200\text{mA}$	400			V
I_{CEX}	Collector-Emitter Cut-Off Current	$V_{CE} = 650\text{V}$ $V_{BE} = -1.5\text{V}$ $T_A = 125^\circ\text{C}$			0.1 1.0	mA
I_{CBO}	Collector Cut-Off Current	$V_{CB} = 650\text{V}$ $I_E = 0$			1.0	
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = -8\text{V}$ $I_C = 0$			2	
$h_{FE}^{(1)}$	Forward-current transfer ratio	$I_C = 1.0\text{A}$ $V_{CE} = 3\text{V}$	10		80	-
		$I_C = 5\text{A}$ $V_{CE} = 3\text{V}$	10		40	
		$T_A = -55^\circ\text{C}$	4			
$V_{CE(sat)}^{(1)}$	Collector-Emitter Saturation Voltage	$I_C = 5\text{A}$ $I_B = 1.0\text{A}$ $T_A = 125^\circ\text{C}$			1.0 2	V
		$I_C = 8\text{A}$ $I_B = 4\text{A}$			2	
$V_{BE(sat)}^{(1)}$	Base-Emitter Saturation Voltage	$I_C = 5\text{A}$ $I_B = 1.0\text{A}$			1.6	

DYNAMIC CHARACTERISTICS

$ h_{fe} $	Magnitude of small signal short circuit forward current transfer ratio	$I_C = 200\text{mA}$ $f = 5\text{MHz}$	$V_{CE} = 10\text{V}$	2	3		-
C_{obo}	Output Capacitance	$V_{CB} = 10\text{V}$ $f = 1.0\text{MHz}$	$I_E = 0$			300	pF
t_d	Delay time	$V_{CC} = 125\text{V}$ $I_C = 5.0\text{A}$ $I_{B1} = -I_{B2} = -1.0\text{A}$				0.1	μs
t_r	Rise Time					0.59	
t_s	Storage Time					4	
t_f	Fall Time					0.42	

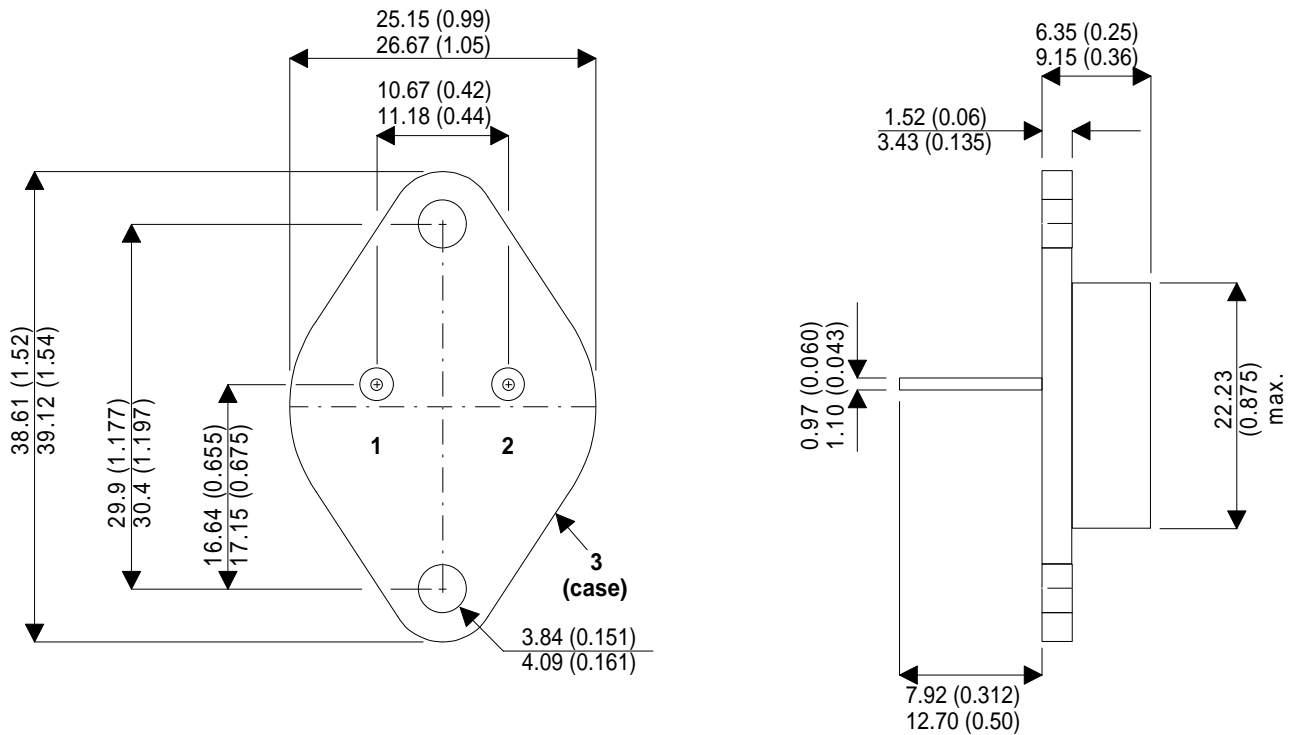
Notes

(1) Pulse Width $\leq 300\mu\text{s}$, $\delta \leq 2\%$

SILICON POWER NPN TRANSISTOR 2N6673

MECHANICAL DATA

Dimensions in mm (inches)



TO3 (TO-204AA) METAL PACKAGE Underside View

Pin 1 - Base

Pin 2 - Emitter

Case - Collector